

**AMENDMENTS TO THE ABSTRACT**

Please replace the Abstract on page 25 with the following replacement paragraph:

-- A process for producing a Schottky junction type semiconductor device ~~is characterized by comprising includes the steps of~~ forming a Schottky electrode on a surface of a silicon carbide epitaxial layer, wherein a Schottky electrode made of molybdenum, tungsten, or an alloy thereof is formed on the surface of the silicon carbide epitaxial layer and is subjected to heat treatment so as to induce an alloying reaction at an interface of the silicon carbide epitaxial layer and the Schottky electrode, thereby forming an alloy layer at the interface, whereby the height of a Schottky barrier is controlled while maintaining an n-factor at a nearly constant low value. --